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Effect of excessive Pb content in the precursor solutions on the properties of the lead acetate derived CH₃NH₃PbI₃ perovskite solar cells



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ABSTRACT

Organic–inorganic $CH_3NH_3PbI_3$ (MAPbI₃) inverted structured perovskite films were prepared using Pb (CH_3COO)₂ (Pb(OAc)₂) and CH_3NH_3I (MAI) as source materials. The structural, optical and photoelectronic properties of the MAPbI₃ films varied with the Pb(OAc)₂/MAI molar ratio. It was found that the Pb(OAc)₂/MAI molar ratio greatly influenced the structure and morphology of the MAPbI₃ films. A suitable amount of excessive Pb(OAc)₂ (about 5 mol% excessive Pb) in the solution made the film smoother with improved film crystallinity. This resulted in enhanced power conversion efficiency (PCE). However, for films derived from solution with low Pb(OAc)₂/MAI or high Pb(OAc)₂/MAI ratio, defects such as pits or pinholes were easily formed with low crystallinity, and hence decreased the lifetime of the carriers and photoelectrical properties of the final solar cells. Using a solution with 5% excessive Pb, inverted structured $CH_3NH_3PbI_3$ perovskite solar cells with PCE of nearly 14% were obtained.

1. Introduction

Organic–inorganic lead halide perovskites have attracted great attention during the past several years as a renewable energy source due to their technological advantages of cost-effective and low temperature synthesis process [1–4]. Power conversion efficiencies (PCE) of photovoltaic devices that contain these materials have increased from around 4% to more than 20% [5–10]. To successfully fabricate reproducible high performance solar cells, the perovskite crystallization process needs to be controlled either by the appropriate choice of processing parameters, techniques and/or by materials selection. The perovskites $CH_3NH_3PbI_3$ (MAPbI₃) and $CH_3NH_3PbI_{3-x}Cl_x$ are normally prepared by the reaction in a solution of CH_3NH_3I (MAI) and PbI_2 in a 1:1 ratio or MAI and $PbCl_2$ in a 3:1 ratio. However, it is more difficult to control the film surface quality when PbI_2 or $PbCl_2$ are used as starting materials. For this case, the perovskite solar cells (PSCs) are always discontinuous, with pinholes of different sizes and no clear grain boundaries [11].

Recently, Zhang et al. prepared PSCs with the lead acetate Pb $(CH_3COO)_2$ (Pb(OAc)₂) as precursor and obtained smooth, pinhole-free perovskite films on TiO₂/FTO/glass substrates; from which, it resulted in devices with a champion power conversion efficiency (PCE) of 15.2% [12]. Moreover, the annealing time was much shorter for the films prepared from Pb(OAc)₂ (5 min at 100 °C), as compared to perovskite

films prepared from $PbCl_2$ and PbI_2 (which needed to be annealed for 2 h and 40 min, respectively) [13,14]. Due to these advantages, the Pb (OAc)₂ derived MAPbI₃ perovskite solar cells showed potential in future applications.

Improvement of the photovoltaic performance and reduction of the hysteresis is another critical issue. A recent investigation by Yang et al. illustrated that the introduction of excessive PbI2 (as second phase into the perovskite matrix) improved the performance of the solar cells. It was reported that PbI₂ formed at the grain boundaries (GBs) could reduce the carrier recombination near GBs [15]. Nazeeruddin and coworkers observed improvements in both the photovoltaic efficiency and stability when PbI₂ and MAI at a non-stoichiometric ratio were used in the precursor solution [16]. On the contrary, some groups believed that the introduction of PbI2 into the perovskite matrix brought about adverse effects on the device properties. Wang et al. reported that the excessive PbI₂ deteriorated the photovoltaic performances [17]. Liu et al. reported that a small amount of excess PbI2 had detrimental effects on the perovskite film stability, although perovskite devices with excess PbI₂ exhibited high initial efficiency [18]. They also reported that the presence of a small amount of excessive PbI2 resulted in the degradation of the perovskite layer under illumination even when stored in an inert atmosphere [18].

Despite the controversy mentioned above, perusal of the literature

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Fig. 1. J-V curves of the samples derived from solutions with different R_{P/M} ratios. Samples in (a) were annealed at 80 °C for 15 min, and samples in (b) were annealed at 90 °C for 5 min.

that reported the effect of the PbI₂ on the performance of PSCs reveals that the perovskite layers were basically prepared from the source materials of PbI₂ and MAI. There are few reports of the effect of excessive Pb on the properties of the perovskite derived from Pb(OAc)₂. When Pb(OAc)₂ is used to synthesize the MAPbI₃, the formation of MAPbI₃ is expressed by formula (1) which has a different formation mechanism than the case when PbI₂ and MAI are used as source materials, as expressed by formula (2) [12]:

$Pb(CH_{3}COO)_{2} + 3CH_{3}NH_{3}I \rightarrow CH_{3}NH_{3}PbI_{3} + 2CH_{3}NH_{3}CH_{3}COO^{\uparrow}$ (1)

$$PbI_2 + CH_3NH_3I \rightarrow CH_3NH_3PbI_3$$
(2)

Therefore, when MAPbI₃ is formed by reaction of MAI with excessive Pb(OAc)₂, a large amount of the CH₃NH₃⁺ (MA) species and I⁻ voids are formed in the films as the main defects. Note these defects are different from the defects in the samples derived from excessive PbI₂. Therefore, a new phenomenon is expected. Triggered by this expectation, we reported on the effect of the excessive Pb ions in the precursor solutions on the properties of Pb(OAc)₂ derived MAPbI₃ PSCs. Considering that the standard n-i-p device configuration requires a high temperature annealing treatment for the TiO₂ layer and always show a pronounced hysteresis during the J-V characterization, the inverted planar perovskite heterojunction using Pb(OAc)₂ as starting materials are prepared in this paper. Results show that suitable amounts of excessive Pb(OAc)₂ in the solution can improve the film crystallinity and surface quality, both of which enhance the PCE of the perovskite layers. However, excessive amount of PbI2 formed in the film degrades the film properties.

2. Experimental

Methylammonium iodide was purchased from Dyesol, lead acetate trihydrate (Pb(OAc)₂·3H₂O) was purchased from Alfa Aesar, and both materials were used as received. To prepare the perovskite precursor solution, 3.0 mmol MAI and 1 mmol Pb(OAc)₂·3H₂O were dissolved in 1 mL anhydrous DMF solution. To investigate the influence of the content of Pb on the film properties, a total of six solutions with different Pb(OAc)₂:MAI ratios ($R_{P/M}$) of 0.975:3, 1.000:3, 1.025:3, 1.050:3, 1.075:3, and 1.100:3 (for short, $R_{P/M} = 0.975$, 1.000, 1.025, 1.050, 1.075 and 1.100, respectively).

Indium-doped tin-oxide (ITO) coated glass substrates were subsequently cleaned with a detergent solution, deionized water, acetone, and isopropyl alcohol, and UV-ozone treated for 10 min. Poly(3,4-ethyl-enedioxythiophene):poly(styrenesulfonate) (PEDOT:PSS, Clevious PVP Al4083 filtered through a 0.45 μ m filter) was spin-coated onto the ITO substrates at 4000 rpm followed by a thermal anneal at 130 °C for 15 min in glovebox. The Pb(OAc)₂:MAI solutions were then spin-coated for 60 s on the PEDOT layers at 4000 rpm followed by thermal

annealing at 80 °C for 15 min or 90 °C for 5 min, resulting in perovskite films with thickness of about 250 nm (as indicated by Fig. S1(a)). After that, phenyl-C₆₁-butyric acid methyl ester (PCBM, Aldrich) dissolved in chlorobenzene with a concentration of 22 mg/mL was spin-coated on top of the perovskite layer at 2000 rpm for 60 s. Finally, the devices were finished with the thermal evaporation of an 80 nm thick Al electrode. This resulted in the inverted planar heterojunction solar cells, as indicated by Fig. S1(b). The size of the substrate is 2.5 cm × 2.5 cm, and the active device area (defined by the overlapping of ITO and Al electrode) is 0.2 cm².

The as-prepared samples were characterized with scanning electron microscopy (SEM-XL30 Environmental FEG (FEI)). X-ray diffraction (XRD) measurements were done with an X-ray Diffractometer using Cu Ka radiation at a step of 0.01°. Surface morphologies and roughness images of the samples were analyzed using Veco Dimension 3100 at. force microscopy in tapping mode. Absorption spectra were recorded using Cary 5000 UV/VIS spectrometer. Current density-voltage (J-V) characteristics of the solar cells were measured with simulated AM 1.5 global solar irradiation (100 mW/cm²) using a xenon-lamp solar simulator (Spectra Physics, Oriel Instruments, USA). The steady sate photoluminescence (PL) spectra of the samples were tested by a Renishaw InVia spectroscopy system with a \times 100 objective lens using a laser source with 488 nm wavelength. The lifetime of charge carriers were detected by a Picosecond Time-Correlated Single Photon Counting (TCSPC) Spectrofluorometer. The PL decay time for perovskite films was monitored at 775 nm with a femtosecond Ti:S laser (Spectra Physics) with a frequency doubler and a pulse selector. The excitation wavelength was fixed at 425 nm. The photoluminescence decay kinetics was fitted to a bi-exponential decay function.

3. Results and discussion

Different $R_{P/M}$ solutions are used to fabricate solar cells with a typical device structure of glass/ITO/PEDOT/perovskite/PCMB/Al. Typical J–V curves of samples annealed at 80 °C and 90 °C are shown in Fig. 1. Results from Fig. 1 show that for samples derived from $R_{P/M} = 0.975$ or 1.000 solutions, the PCE is basically not more than 11%. For samples annealed at 80 °C, the PCE value increases to 13.82% with the $R_{P/M}$ increase from 1.000 to 1.100, and then decreases to 10.83% at P/M = 1.100. The highest PCE value at $R_{P/M} = 1.050$ is obtained by simultaneously improving two factors: J_{sc} of 21.620 mA cm⁻², V_{oc} of 0.958 V. Although the PCE of samples annealed at 90 °C is lower than that of the 80 °C-annealed samples, the similar trend is obtained for both groups of samples. From the data listed in Table 1, it shows that for both groups of samples, samples derived from P/M = 1.05 solution show the highest PCE, J_{sc} , and V_{oc} . The FF, however, basically increases with $R_{P/M}$, which is same to the results reported by Nazeeruddin et al.

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